isc N-Channel MOSFET Transistor   IRF034

DESCRIPTION

• Drain Current I_D=25A@ T_C=25℃

• Drain Source Voltage-

  : V_{DSS}= 60V(Min)

• Static Drain-Source On-Resistance

  : $R_{DS(on)}$ = 0.05 Ω (Max)
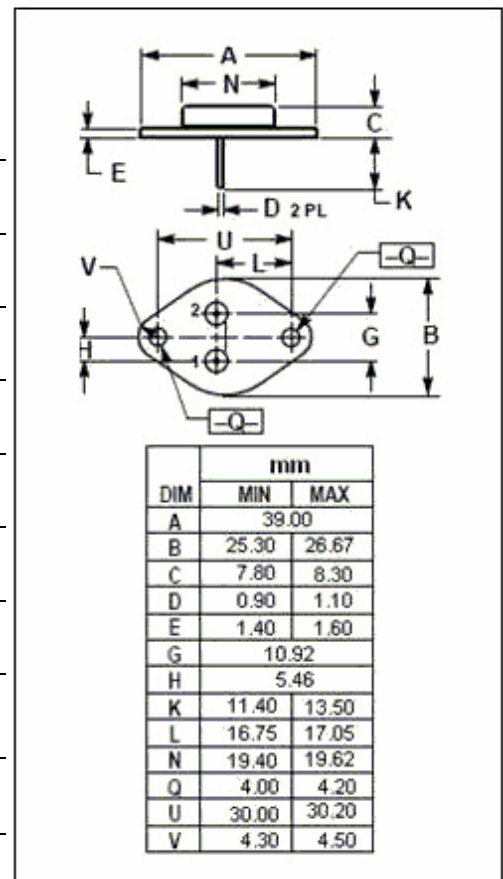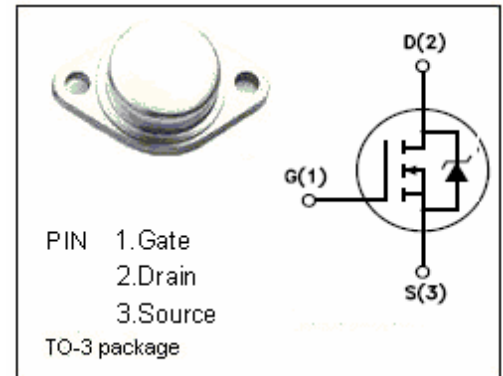
• Simple Drive Requirements

APPLICATIONS

• Switching power supplies

• Motor controls,Inverters and Choppers

• Audio amplifiers and high energy pulse circuits.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	60	V
V_{GS}	Gate-Source Voltage	$\pm$20	V
I_D	Drain Current-continuous@ TC=25℃	25	A
P_{tot}	Total Dissipation@TC=25℃	75	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\,j-c}$	Thermal Resistance,Junction to Case	1.67	℃/W
$R_{th\,j-a}$	Thermal Resistance,Junction to Ambient	30	℃/W

PIN   1.Gate
      2.Drain
      3.Source
TO-3 package

DIM	mm MIN	mm MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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• **ELECTRICAL CHARACTERISTICS (T$_C$=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V$_{(BR)DSS}$	Drain-Source Breakdown Voltage	V$_{GS}$=0; I$_D$=1mA	60			V
V$_{GS(TH)}$	Gate Threshold Voltage	V$_{DS}$= V$_{GS}$; I$_D$=250μA	2.0		4.0	V
R$_{DS(ON)}$	Drain-Source On-stage Resistance	V$_{GS}$=10V; I$_D$=16A			0.05	Ω
I$_{GSS}$	Gate Source Leakage Current	V$_{GS}$=±20V;V$_{DS}$=0			±100	nA
I$_{DSS}$	Zero Gate Voltage Drain Current	V$_{DS}$=48V; V$_{GS}$=0			25	μA
V$_{SD}$	Diode Forward Voltage	I$_S$=25A; V$_{GS}$=0			1.8	V
C$_{iss}$	Input Capacitance	V$_{DS}$=25V; V$_{GS}$=0V; f$_T$=1MHz		1300		pF
C$_{rss}$	Reverse Transfer Capacitance			100		
C$_{oss}$	Output Capacitance			650		
t$_r$	Rise Time	I$_D$=25A; V$_{DD}$=30V; R$_G$=7.5Ω			110	ns
t$_{d(on)}$	Turn-on Telay Time				21	
t$_f$	Fall Time				80	
t$_{d(off)}$	Turn-off Delay Time				53	

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